

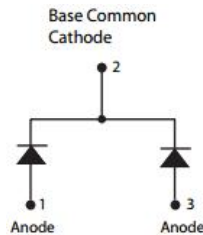
SDUR2060WTA ULTRAFAST RECTIFIER



Applications:

- Antiparallel diode for high frequency switching devices
- Anti saturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating and melting
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

Circuit Diagram



Features:

- Ultra-Fast switching
- High current capability
- Low reverse leakage current
- High surge current capability
- Terminals finish: 100% Pure Tin
- This is a Pb – free device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage	V_{RRM}	-	600	V
Working Peak Reverse Voltage	V_{RWM}			
DC Blocking Voltage	V_R			
Average Rectified Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_c=100^\circ\text{C}$, rectangular wave form	10(Per Leg) 20(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current(Per Leg)	I_{FSM}	8.3ms, Half Sine pulse	100	A

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Typical Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	0.95	$^\circ\text{C/W}$
Approximate Weight	wt	-	6.28	g
Case Style	TO-247AD			

Electrical Characteristics:

Characteristics	Symbol	Condition	Typ.	Max.	Units
Forward Voltage Drop (Per Leg)*	V _{F1}	@ 10A, Pulse, T _J = 25°C	1.67	2.2	V
	V _{F2}	@ 10A, Pulse, T _J = 125°C	1.59	2.0	V
Reverse Current (Per Leg)*	I _{R1}	@V _R = rated V _R , T _J = 25°C	0.3	10	μA
	I _{R2}	@V _R = rated V _R , T _J = 125°C	150	500	μA
Reverse Recovery Time(Per Leg)	t _{rr}	I _F =500mA, I _R =1A, and I _{rm} =250mA	25	35	ns
Reverse Recovery Time(Per Leg)	t _{rr}	I _F = 10A, diF/dt = -200A/μs V _R = 400V, T _J = 25°C	60	-	ns
Reverse Recovery Charge(Per Leg)	Q _{rr}		108	-	nC
Reverse Recovery Current(Per Leg)	I _{RRM}		4	-	A
Reverse Recovery Time(Per Leg)	t _{rr}	I _F = 10A, diF/dt = -200A/μs V _R = 400V, T _J = 125°C	126	-	ns
Reverse Recovery Charge(Per Leg)	Q _{rr}		290	-	nC
Reverse Recovery Current(Per Leg)	I _{RRM}		5	-	A
Reverse Recovery Time(Per Leg)	t _{rr}	I _F = 1A, diF/dt = -100A/μs V _R = 30V, T _J = 25°C	34	-	ns
Reverse Recovery Charge(Per Leg)	Q _{rr}		32	-	nC
Reverse Recovery Current(Per Leg)	I _{RRM}		2.0	-	A
Reverse Recovery Time(Per Leg)	t _{rr}	I _F = 1A, diF/dt = -100A/μs V _R = 30V, T _J = 125°C	53	-	ns
Reverse Recovery Charge(Per Leg)	Q _{rr}		69	-	nC
Reverse Recovery Current(Per Leg)	I _{RRM}		3	-	A
Reverse Recovery Time(Per Leg)	t _{rr}	I _F = 10A, diF/dt = -100A/μs V _R = 30V, T _J = 25°C	55	-	ns
Reverse Recovery Charge(Per Leg)	Q _{rr}		70	-	nC
Reverse Recovery Current(Per Leg)	I _{RRM}		3	-	A
Reverse Recovery Time(Per Leg)	t _{rr}	I _F = 10A, diF/dt = -100A/μs V _R = 30V, T _J = 125°C	86	-	ns
Reverse Recovery Charge(Per Leg)	Q _{rr}		155	-	nC
Reverse Recovery Current(Per Leg)	I _{RRM}		4	-	A

* Pulse width < 300 μs, duty cycle < 2%

Ratings and Characteristics Curves

Figure 1
Typical Forward Characteristics

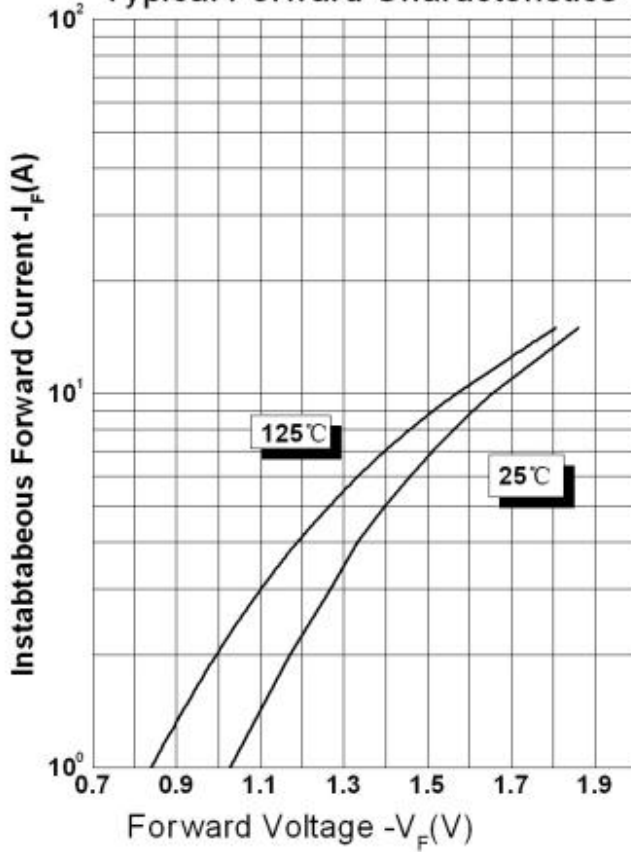


Figure 2
Typical Reverse Characteristics

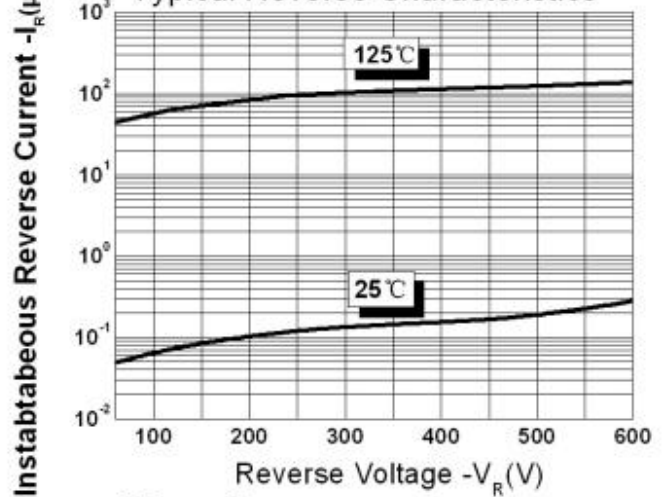
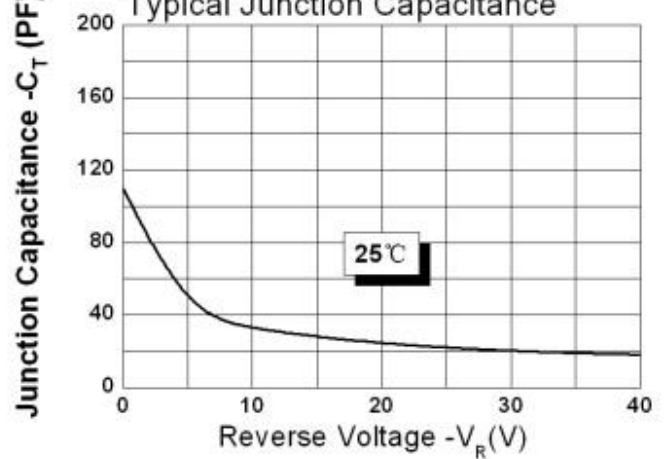


Figure 3
Typical Junction Capacitance



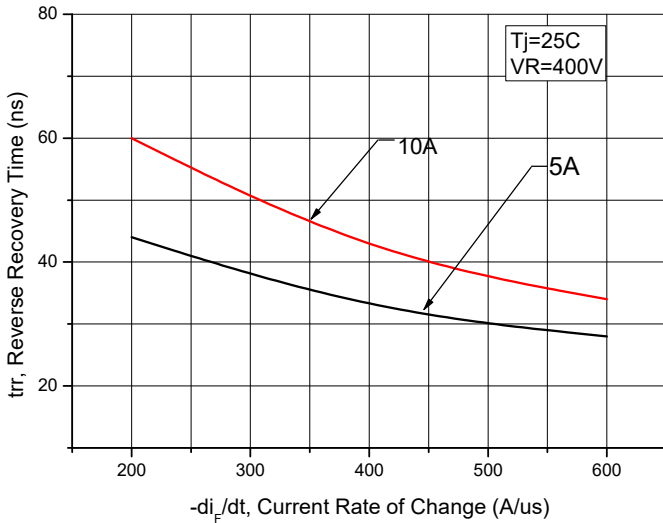


Figure 4. Reverse Recovery Time vs. Current Rate of Change

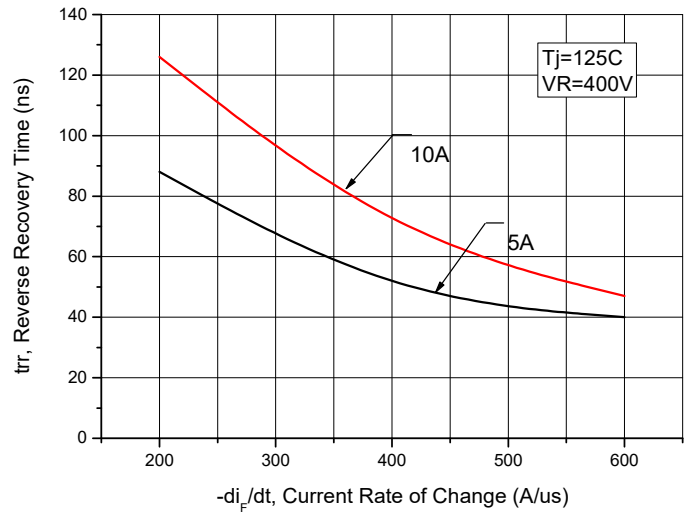


Figure 5. Reverse Recovery Time vs. Current Rate of Change

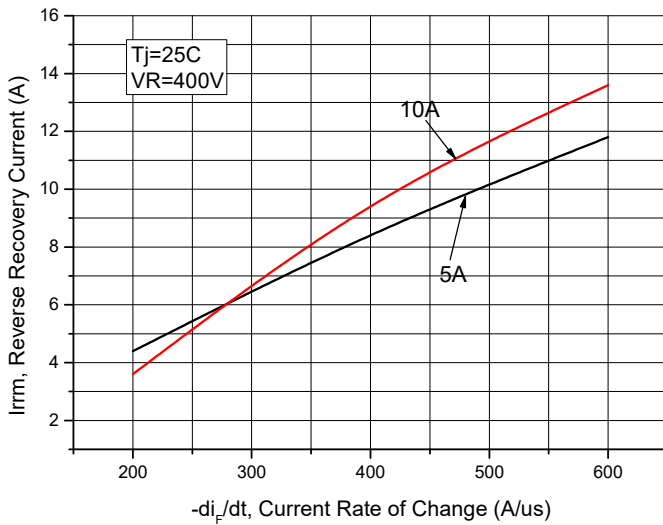


Figure 6. Reverse Recovery Current vs. Current Rate of Change

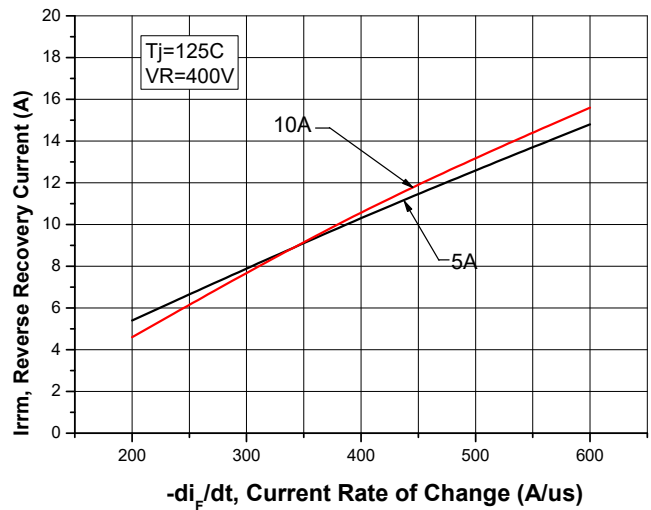


Figure 7. Reverse Recovery Current vs. Current Rate of Change

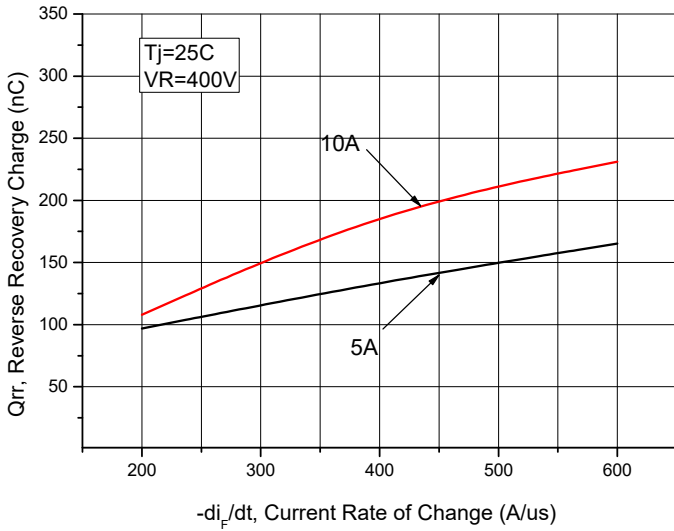


Figure 8. Reverse Recovery Charge vs. Current Rate of Change

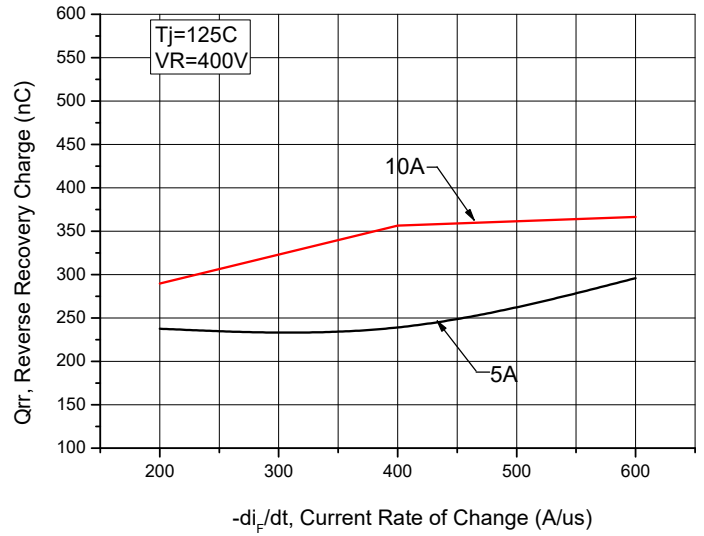


Figure 9. Reverse Recovery Charge vs. Current Rate of Change

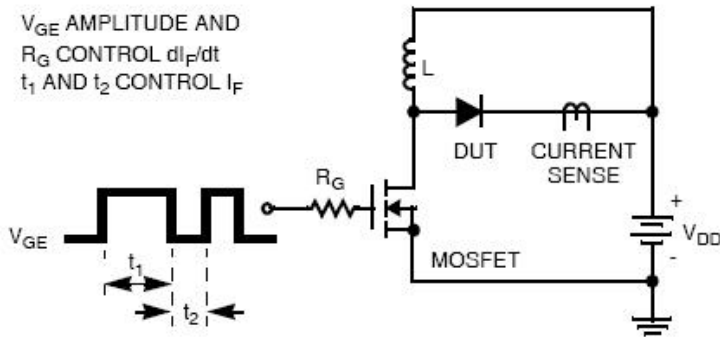


Figure 10. Diode Test Circuit

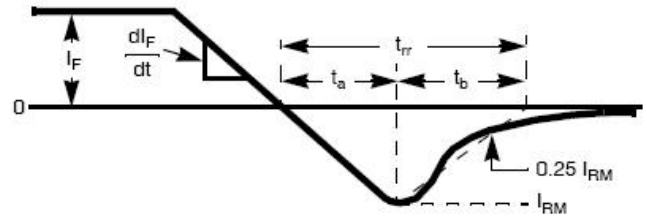
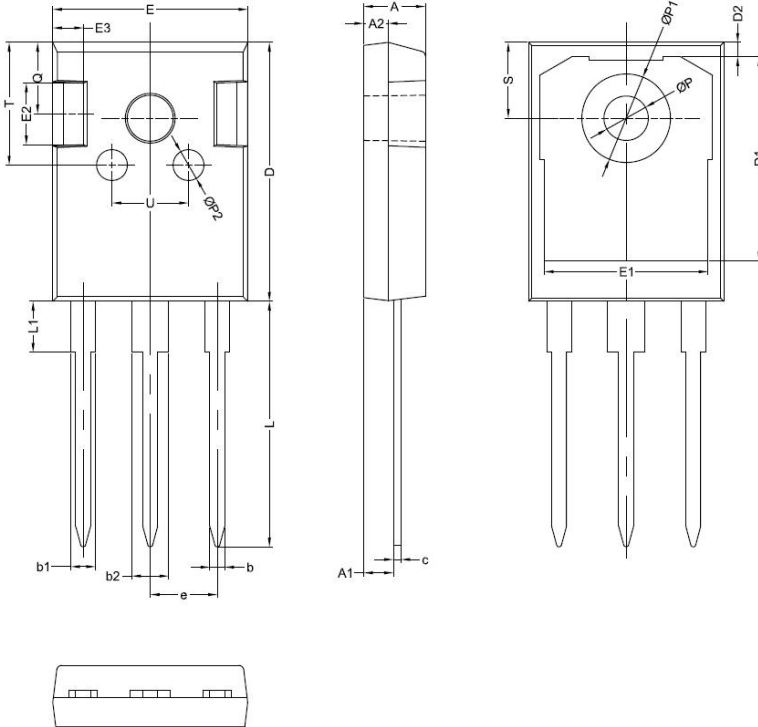


Figure 11. Diode Reverse Recovery Waveform

Mechanical Dimensions TO-247AD



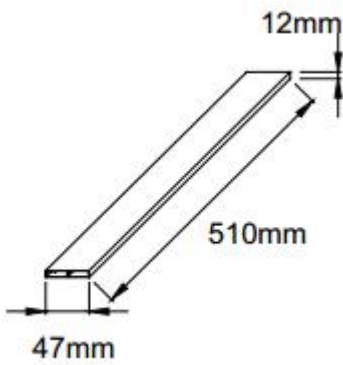
SYMBOL	Millimeters		
	MIN.	TYP.	MAX.
A	4.80	5.00	5.20
A1	2.20	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.40
b1	1.80	2.00	2.20
b2	2.80	3.00	3.20
c	0.50	0.60	0.75
D	20.30	21.00	21.20
D1		16.55	
D2		1.20	
E	15.45	15.80	16.00
E1		13.30	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.70
L1		4.13	
P	3.50	3.60	3.70
P1	7.1		7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	

Ordering Information:

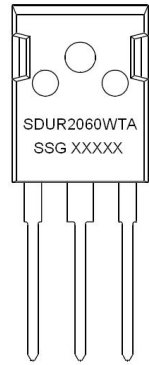
Device	Package	Shipping
SDUR2060WTA	TO-247AD(Pb-Free)	25pcs / tube

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging Specification.

Tube Specification



Marking Diagram



Where XXXXX is YYWWL

- SDUR = Device Type
- 20 = Forward Current (20A)
- 60 = Reverse Voltage (600V)
- WTA = Configuration
- SSG = SSG
- YY = Year
- WW = Week
- L = Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0



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